中国科学院半导体研究所

黄昆半导体科学技术论坛

第397期讲座

报告题目： Wide Bandgap Compound Semiconductors for Future of Moore's Law

报 告 人： Xiaohang Li (KAUST, Saudi Arabia)

Abstract: (Ultra) wide bandgap compound semiconductors including AlN, GaN, Ga_2O_3 and In_2O_3 have attracted enormous interests. They offer markedly larger figures of merits for power and RF applications than other known semiconductors. Additionally, they can be applied for vastly impactful quantum information technologies and deep UV/visible optoelectronics. Moreover, they could be promising for More Moore, More than Moore, and Beyond Moore applications. This seminar will cover the latest material, device and IC research based on (U)WBG semiconductors for the future of Moore's Law.

Bibliography: Xiaohang Li is an Associate Professor of Electrical and Computer Engineering, and the founding task force chair of Technology Innovation and Entrepreneurship Program at KAUST. He also serves as the Associate Director of KAUST Innovation Hub. He obtained Ph.D. in Electrical Engineering from Georgia Institute of Technology. His research focuses on cutting-edge research on (ultra) wide bandgap semiconductors for next-generation electronics and photonics. He has authored over 160 journal papers in prestigious journals such as Nature Electronics, Advanced Materials, Light: Science & Applications, Optica. He has also authored more than 250 conference publications and presentations, and holds >20 issued patents. He is the recipient of several prestigious awards including the Harold M. Manasevit Young Investigator Award from the American Association for Crystal Growth, the SPIE D. J. Lovell Scholarship, IEEE Photonics Graduate Student Fellowship. He is an Associate Editor of Photonics Research, an editorial member of Journal of Semiconductor, and as a committee member of several leading conferences including IWN and ICNS.

时　间： 2024年11月6号（星期二）上午10:00

地　点： 中国科学院半导体研究所3号楼320会议室

联系人： 尚晓轩 82304453